



# **Ultrahigh-Speed Switching Applications**

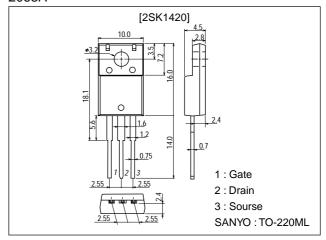
### **Features**

- · Low ON-state resistance.
- · Ultrahigh-speed switching.
- · Converters.
- · Micaless package facilitating mounting.

# **Package Dimensions**

unit:mm

2063A



# **Specifications**

## Absolute Maximum Ratings at Ta = 25°C

| Parameter                   | Symbol           | Conditions             | Ratings     | Unit |
|-----------------------------|------------------|------------------------|-------------|------|
| Drain-to-Source Voltage     | V <sub>DSS</sub> |                        | 60          | V    |
| Gate-to-Source Voltage      | VGSS             |                        | ±20         | V    |
| Drain Current (DC)          | ID               |                        | 25          | Α    |
| Drain Current (Pulse)       | I <sub>DP</sub>  | PW≤10μs, duty cycle≤1% | 100         | Α    |
| Allowable Power Dissipation | PD               | Tc=25°C                | 30          | W    |
|                             |                  |                        | 2.0         | W    |
| Channel Temperature         | Tch              |                        | 150         | °C   |
| Storage Temperature         | Tstg             |                        | -55 to +150 | °C   |

#### Electrical Characteristics at Ta = 25°C

| Parameter                                  | Symbol              | Conditions                                | Ratings |       |       | Unit |
|--|---------------------|---|---------|-------|-------|------|
|  |                     |   | min     | typ   | max   |      |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS            | I <sub>D</sub> =1mA, V <sub>GS</sub> =0   | 60      |       |       | V    |
| Zero-Gate Voltage Drain Current            | IDSS                | V <sub>DS</sub> =60V, V <sub>GS</sub> =0  |         |       | 100   | μA   |
| Gate-to-Source Leakage Current             | IGSS                | V <sub>GS</sub> =±20V, V <sub>DS</sub> =0 |         |       | ±100  | nA   |
| Cutoff Voltage                             | VGS(off)            | $V_{DS}$ =10V, $I_D$ =1mA                 | 1.5     |       | 2.5   | V    |
| Forward Transfer Admittance                | yfs                 | V <sub>DS</sub> =10V, I <sub>D</sub> =15A | 10      | 15    |       | S    |
| Static Drain-to-Source ON-State Resistance | R <sub>DS(on)</sub> | I <sub>D</sub> =15A, V <sub>GS</sub> =10V |         | 0.035 | 0.045 | Ω    |

 $(Note)\ Be\ careful\ in\ handling\ the\ 2SK1420\ because\ it\ has\ no\ protection\ diode\ between\ gate\ and\ source.$ 

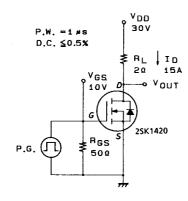
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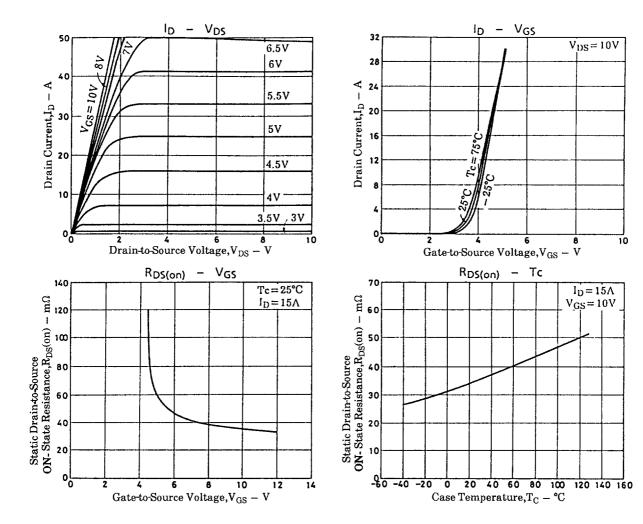
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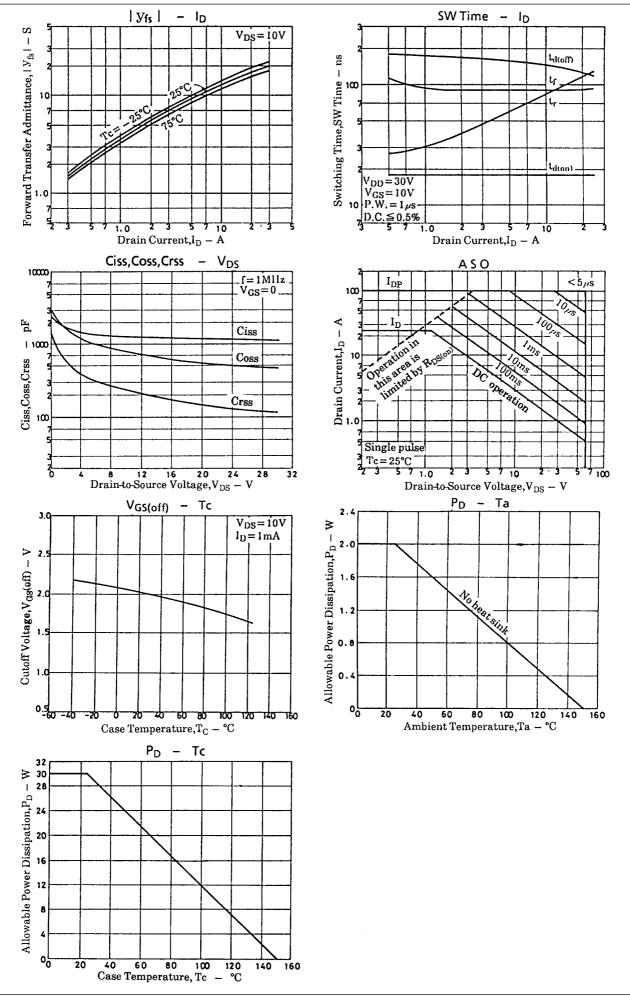
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| Parameter                    | Symbol             | Conditions  | Ratings |      |     | Unit |
|------------------------------|--------------------|---|---------|------|-----|------|
|                              |                    |   | min     | typ  | max | Oill |
| Input Capacitance            | Ciss               | V <sub>DS</sub> =20V, f=1MHz                                      |         | 1200 |     | pF   |
| Output Capacitance           | Coss               | V <sub>DS</sub> =20V, f=1MHz                                      |         | 550  |     | pF   |
| Reverse Transfer Capacitance | Crss               | V <sub>DS</sub> =20V, f=1MHz                                      |         | 150  |     | pF   |
| Turn-ON Delay Time           | t <sub>d(on)</sub> | $I_{D}$ =15A, $V_{GS}$ =10V, $V_{DD}$ =30V, $R_{GS}$ =50 $\Omega$ |         | 18   |     | ns   |
| Rise Time                    | t <sub>r</sub>     | $I_{D}$ =15A, $V_{GS}$ =10V, $V_{DD}$ =30V, $R_{GS}$ =50 $\Omega$ |         | 102  |     | ns   |
| Turn-OFF Delay Time          | td(off)            | $I_{D}$ =15A, $V_{GS}$ =10V, $V_{DD}$ =30V, $R_{GS}$ =50 $\Omega$ |         | 130  |     | ns   |
| Fall Time                    | t <sub>f</sub>     | $I_{D}$ =15A, $V_{GS}$ =10V, $V_{DD}$ =30V, $R_{GS}$ =50 $\Omega$ |         | 90   |     | ns   |
| Diode Forward Voltage        | V <sub>SD</sub>    | I <sub>S</sub> =25A, V <sub>GS</sub> =0                           |         |      | 1.8 | V    |

## **Switching Time Test Circuit**







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